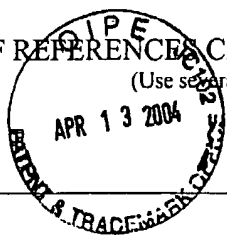





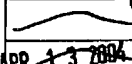
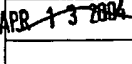
<b>LIST OF REFERENCES CITED BY APPLICANT</b> (Use several sheets if necessary)	ATTY DOCKET NO.	APPLICATION NO
	060937-0215-US	10/665,417
	APPLICANT Robert J. SMALL et al.	
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	September 22, 2003	1755



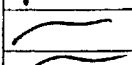
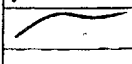
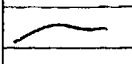
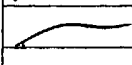
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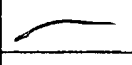
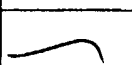


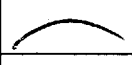
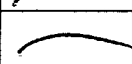

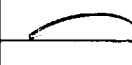
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	C02	"Dissolution of Copper and Tantalum Films in Hydroxylamine Based Silica Slurries Under CMP Conditions" by Wayne Huang et al., 1999 Joint Intl. Meeting, Oct. 17-2
	C03	"Challenges of electroplated Copper Film and Device Characteristics for Copper Slurry Design, Maria L. Peterson et al., Semiconductor Fab Tech, Oct. 19, 1999, 5 pages
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EXAMINER

DATE CONSIDERED

8/17/07

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.